



ZP1230- RECTIFIER DIODE

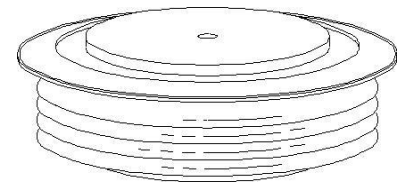
3800-4500V_{RRM}

GENERAL PURPOSE HIGH POWER STANDARD RECTIFIER

Features:

- . All diffused structure
- . High surge rating
- . Blocking capability up to 4500 volts
- . Ceramic housing hermetic package
- . Pressure assembled device

D8C



ELECTRICAL CHARACTERISTICS AND RATINGS

Reverse Blocking

Device Type	V _{RRM} (1)	V _{RSM} (1)
ZP1230-38	3800	3900
ZP1230-40	4000	4100
ZP1230-42	4200	4300
ZP1230-44	4400	4500
ZP1230-45	4500	4600

V_{RRM} = Repetitive peak reverse voltage

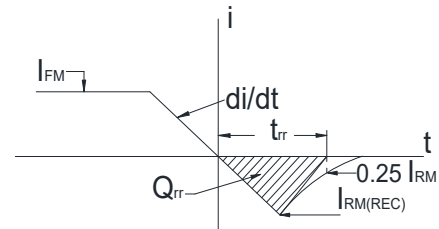
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage current	I _{RRM}	5mA 60 mA (3)
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Notes:

All ratings are specified for T_j=25 °C, unless otherwise stated

- (1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range 0 to +150 °C.
- (2) 10 msec. max. pulse width
- (3) Maximum value for T_j = 150 °C.
- (4) See parameter definition below :



reverse recovery characteristic

Conducting - on state

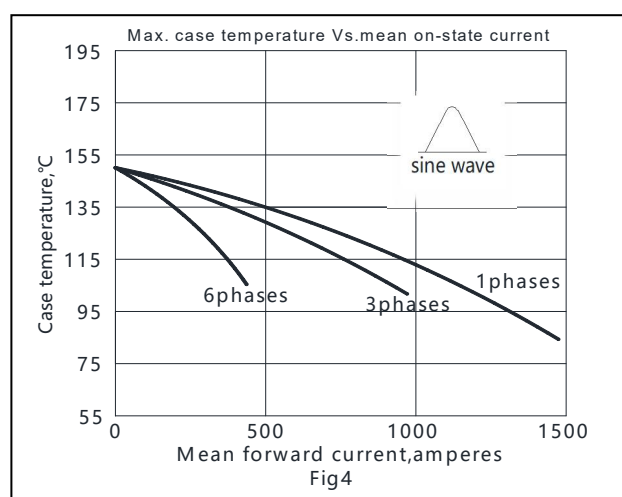
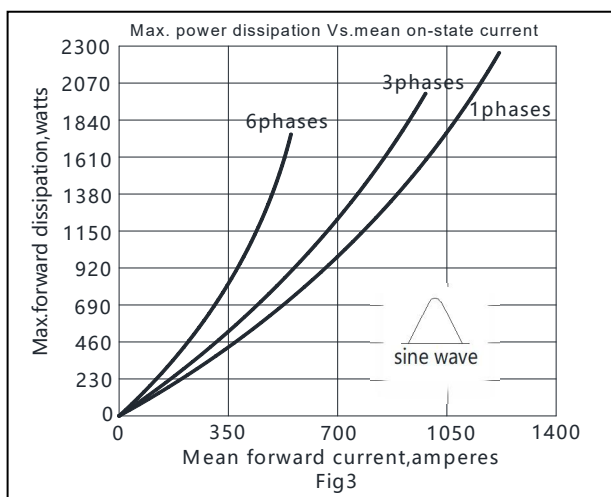
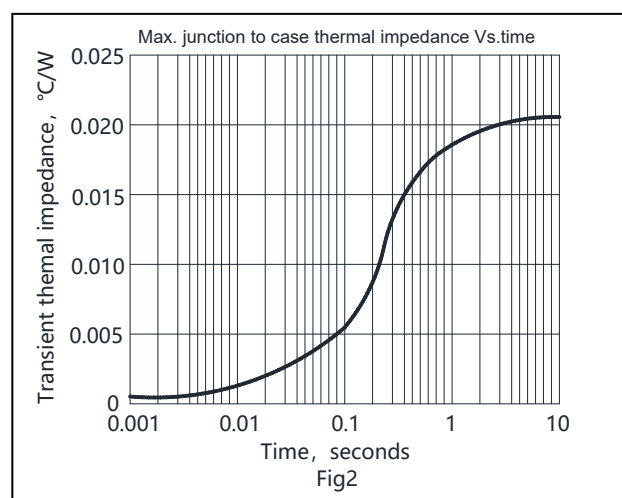
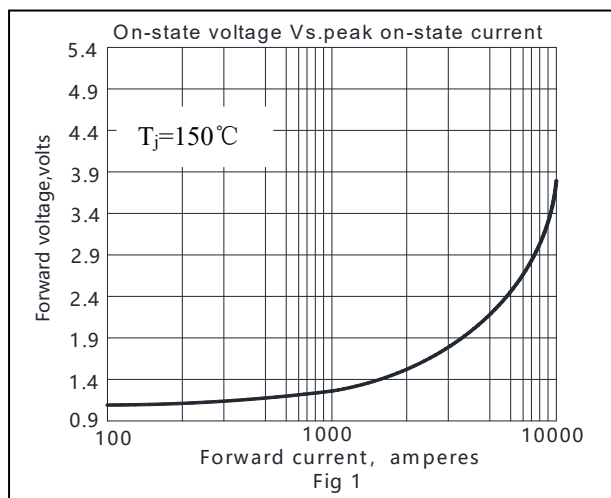
Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average forward current	I _{F(AV)}		1230		A	Sinewave 180°, T _c =100°C
RMS forward current	I _{FRMS}		1931		A	Nominal value
Peak one cycle surge (non repetitive) current	I _{FSM}		18450		A	10 msec (50Hz), sinusoidal wave-shape, 180° conduction, T _j =150°C
I square t	I ² t		17×10 ⁵		A ² s	10 msec
Peak forward voltage	V _{FM}		2.0		V	I _{FM} = 3000A; T _j =25°C
Threshold voltage	V _{FO}		0.96		V	T _j =150°C, I=0.5 π I _{F(AV)} to 1.5 π I _{F(AV)}
Slope resistance	r _F		0.29		mΩ	T _j =150°C, I=0.5 π I _{F(AV)} to 1.5 π I _{F(AV)}
Reverse Recovery Current (4)	I _{RM(REC)}				A	I _{FM} = 500 A; di/dt = -10 A/s; T _{jmax}
Reverse Recovery Charge (4)	Q _{rr}			4500	μC	I _{FM} = 500 A; di/dt = -10 A/s; T _{jmax}
Reverse Recovery Time (4)	t _{rr}				μs	I _{FM} = 500 A; di/dt = -10 A/s; T _{jmax}

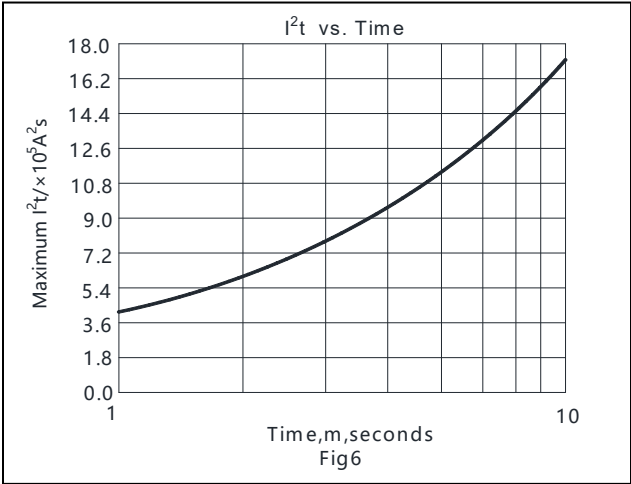
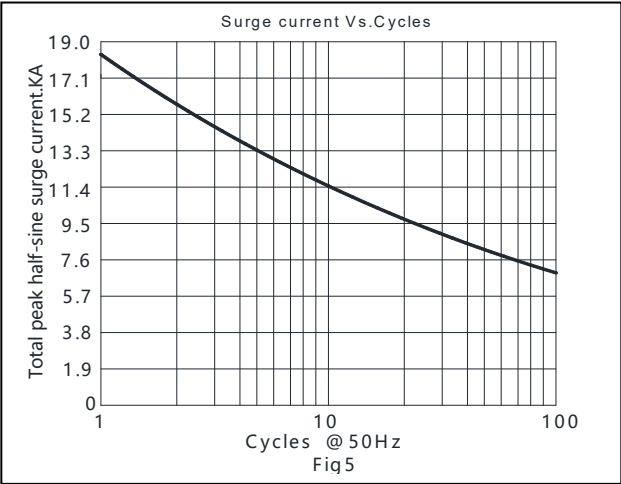
Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Operating temperature	T_j	-40	+150		°C	
Storage temperature	T_{stg}	-40	+150		°C	
Thermal resistance - junction to case	$R_{\theta(j-c)}$		0.022		°C/W	Double sided cooled
Thermal resistance - case to heatsink	$R_{\theta(c-s)}$		0.005		°C/W	Double sided cooled
Mounting force	F	22	27	25	kN	
Weight	m			0.46	kg.	

* Mounting surfaces smooth, flat and greaseless

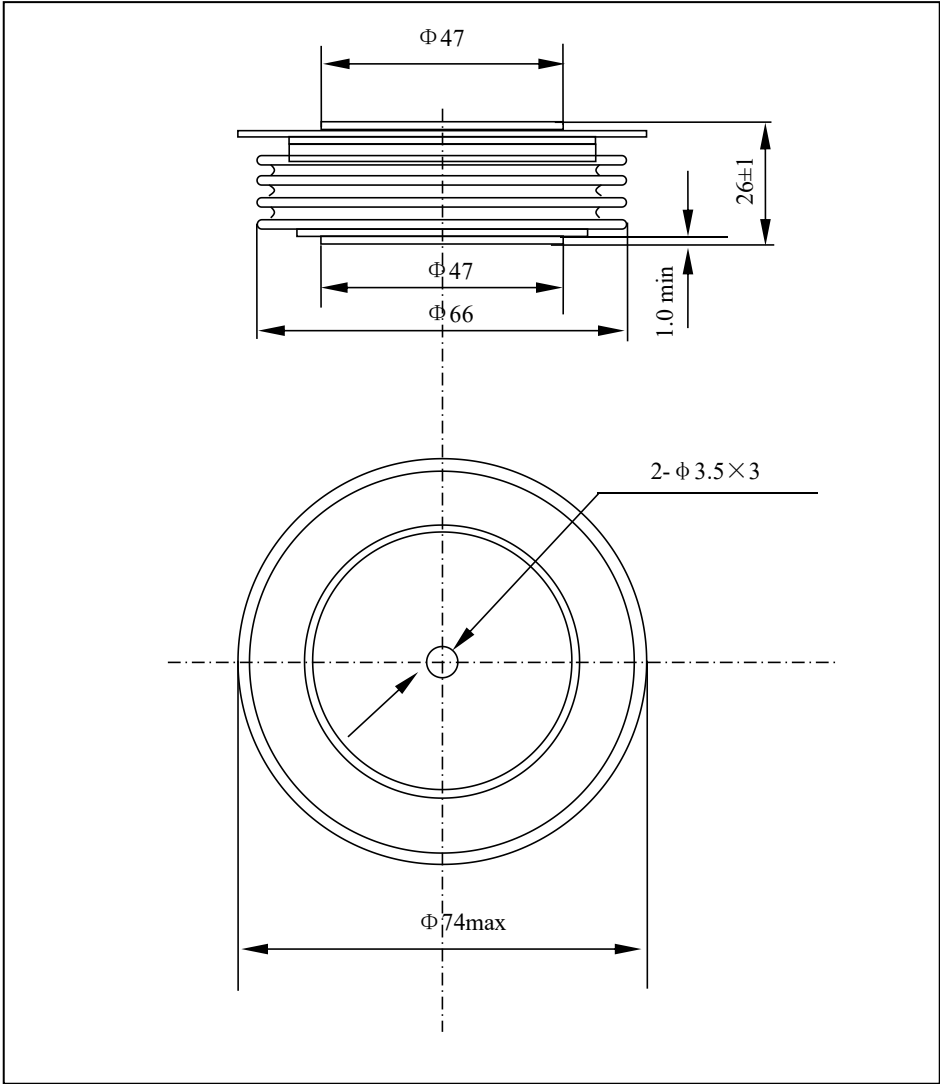
Graph

ZP1230-RECTIFIER DIODE





CASE OUTLINE AND DIMENSIONS



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